



USSP4240

PNP EPITAXIAL SILICON TRANSISTOR

-40V, -2.0A PNP LOW $V_{CE(SAT)}$ TRANSISTOR

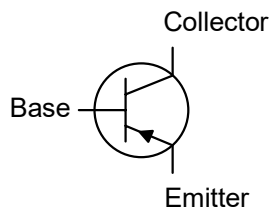
DESCRIPTION

The UTC **USSP4240** is an PNP low $V_{CE(SAT)}$ Breakthrough.

FEATURES

- * Low collector-emitter saturation voltage $V_{CE(SAT)}$
- * High collector current capability: I_C and I_{CM}
- * Higher efficiency leading to less heat generation
- * Reduced printed-circuit board requirements
- * Complement: USSN4240
- * Green Product

EQUIVALENT CIRCUIT



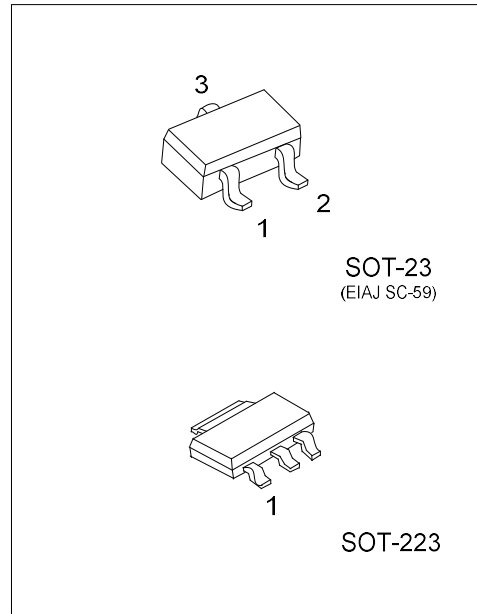
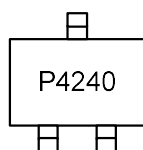
ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Packing
		1	2	3	
USSP4240G-AE3-R	SOT-23	B	E	C	Tape Reel

Note: Pin Assignment: B: Base C: Collector E: Emitter

USSP4240G-AE3-R	(1) Packing Type	(1) R: Tape Reel
	(2) Package Type	(2) AE3: SOT-23
	(3) Green Package	(3) G: Halogen Free and Lead Free

MARKING



■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	DC	I _C	-2
	Peak	I _{CM}	-4
Power Dissipation (T _A ≤ 25°C)	P _D	0.35	W
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-65 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Device mounted on a FR4 printed-circuit board, single-sided copper; tin-plated, mounting pad for collector 1 cm².

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ _{JA}	357	°C/W
Junction to Case	θ _{JC}	100	°C/W

Note: Device mounted on a FR4 printed-circuit board, single-sided copper; tin-plated, mounting pad for collector 1 cm².

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-100μA, I _E =0	-40			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =-1mA, I _B =0	-40			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =-100μA, I _C =0	-5			V
Collector-Base Cut-Off Current	I _{CBO}	V _{CB} =-40V, I _E =0			-100	nA
		V _{CB} =-40V, I _E =0, T _J =150°C			-50	μA
Collector-Emitter Cut-Off Current	I _{CES}	V _{CE} =-40V, V _{BE} =0			-100	nA
Emitter-Base Cut-Off Current	I _{EBO}	V _{EB} =-5V, I _C =0			-100	nA
Collector-Emitter Saturation Voltage (Note)	V _{CE(SAT)}	I _C =-500mA, I _B =-50mA			-100	mV
		I _C =-1A, I _B =-50mA			-250	mV
		I _C =-1A, I _B =-100mA			-200	mV
		I _C =-2A, I _B =-100mA			-450	mV
		I _C =-2A, I _B =-200mA			-400	mV
Base-Emitter Saturation Voltage (Note)	V _{BE(SAT)}	I _C =-500mA, I _B =-50mA			-1	V
		I _C =-1A, I _B =-50mA			-1.05	V
		I _C =-2A, I _B =-100mA			-1.15	V
		I _C =-2A, I _B =-200mA			-1.2	V
Base-Emitter Turn-On Voltage(Note)	V _{BE(ON)}	I _C =-2A, V _{CE} =-2V			1	V
Dc Current Gain (Note)	h _{FE}	V _{CE} =-2V, I _C =-100mA	250			
		V _{CE} =-2V, I _C =-500mA	230			
		V _{CE} =-2V, I _C =-1A	180			
		V _{CE} =-2V, I _C =-2A	50			
Transition Frequency	f _T	V _{CE} =-10V, I _C =-50mA, f=100MHz	100			MHz

Note: Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤ 2%.

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